AlGaInP/GaAs Super Red Chip ---TK0509SRN

1. Scope

- The specification applies to AlGaInP LED chips.
- Type : TK0509SRN.

2. Structure

- AlGaInP/GaAs super red LED chip.
- Electrode P (anode) side : Aluminum or Gold.
- Electrode N (cathode) side : Gold alloy.

3. Size

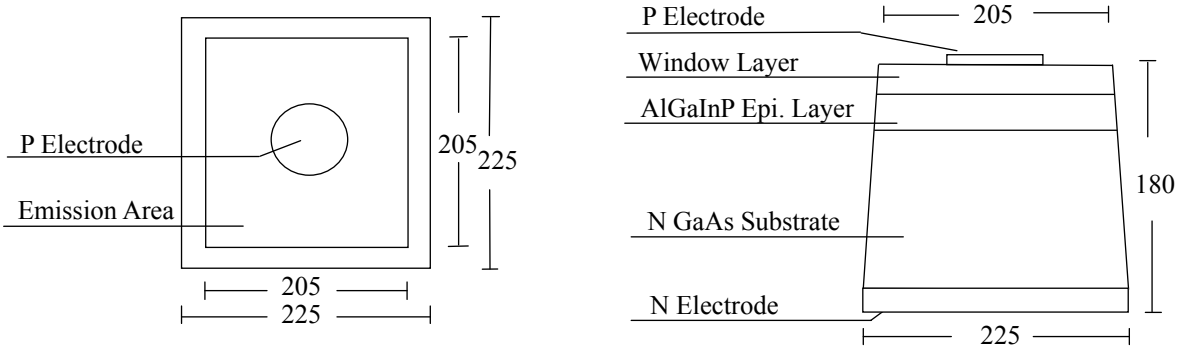
- Chip size : 225μm × 225μm
- Chip height : 180μm ± 30μm
- Pattern drawing : per fig. 1

4. Electro-Optical Characteristics

(Ta =+25 ℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	I_F =20 mA		2.00	2.30	V
Reverse Voltage	V_R	I_R =10 μA	5			V
Luminous Intensity	I_V	I_F =20 mA		※		mcd
Wavelength	λ_p / λ_d	I_F =20 mA		645/631		nm
Spectrum Width of Half Value	Δ λ	I_F =20 mA		20		nm

※
- Rank D : min.≧20.0, 25.0≦avg.＜35.0
- Rank E : min.≧25.0, 35.0≦avg.＜45.0
- Rank F : min.≧35.0, 45.0≦avg.＜55.0
- Rank G : min.≧40.0, 55.0≦avg.＜65.0
- Rank H : min.≧50.0, 65.0≦avg.＜75.0
- Rank I : min.≧60.0, 75.0≦avg.＜85.0
- Rank J : min.≧70.0, 85.0≦avg.＜95.0



Unit：μm

fig. 1

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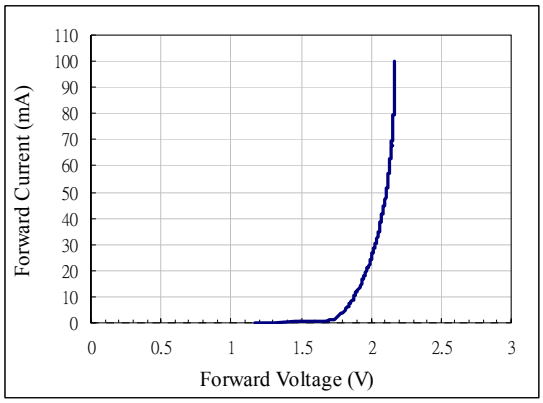
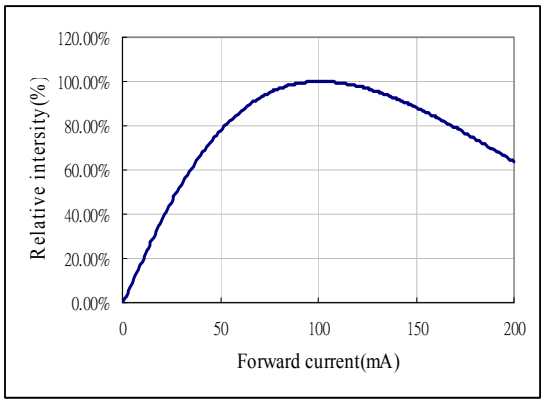
Electro-Optical Characteristics Curve

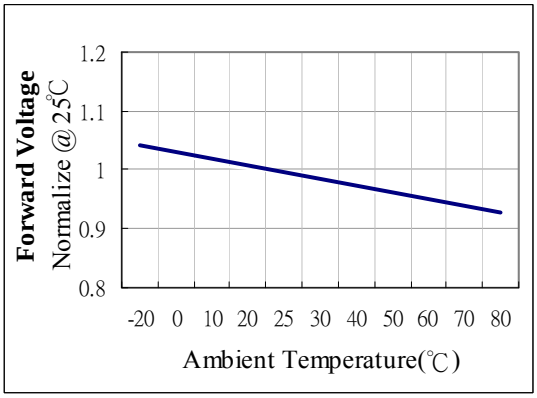
Forward current vs. Forward voltage



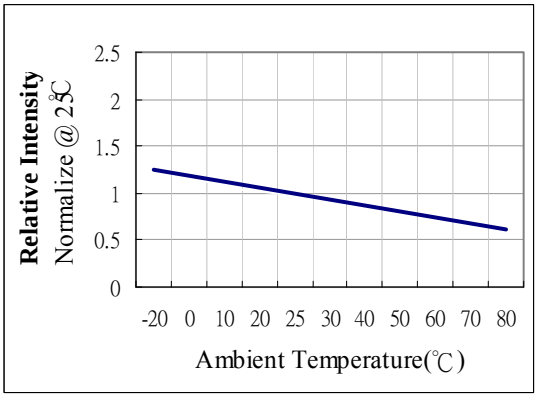
Relative intensity vs. Forward current



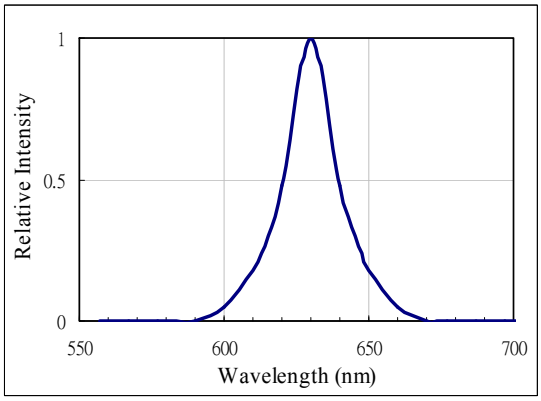
Forward voltage vs. Temperature



Relative intensity vs. Temperature



Relative intensity vs. Wavelength



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